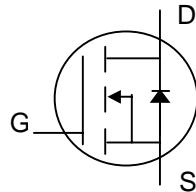


N-CHANNEL ENHANCEMENT-MODE POWER MOSFET

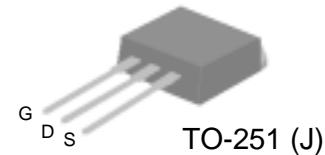
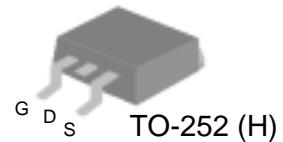
Dynamic dv/dt rating
 Repetitive-avalanche rated
 Fast switching
 Simple drive requirement



BV_{DSS} 600V
 $R_{DS(ON)}$ 8Ω
 I_D 1.6A

Description

The SSM01N60H is supplied in the industry-standard TO-252 package, which is widely preferred for commercial and industrial surface mount applications, and is well suited for AC/DC converters. The through-hole version (SSM01N60J) is available for low-footprint applications.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	600	V
V_{GS}	Gate-Source Voltage	± 30	V
$I_D @ T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	1.6	A
$I_D @ T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	1	A
I_{DM}	Pulsed Drain Current ¹	6	A
$P_D @ T_C=25^\circ C$	Total Power Dissipation	39	W
	Linear Derating Factor	0.31	W/°C
E_{AS}	Single Pulse Avalanche Energy ²	13	mJ
I_{AR}	Avalanche Current	1.6	A
E_{AR}	Repetitive Avalanche Energy	0.5	mJ
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Value	Unit
R_{thj-c}	Thermal Resistance Junction-case	Max. 3.2	°C/W
R_{thj-a}	Thermal Resistance Junction-ambient	Max. 110	°C/W

Electrical Characteristics @ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$, $I_D=250\mu\text{A}$	600	-	-	V
$\Delta \text{BV}_{\text{DSS}}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	-	0.6	-	$\text{V}/^\circ\text{C}$
$R_{\text{DS(ON)}}$	Static Drain-Source On-Resistance	$V_{\text{GS}}=10\text{V}$, $I_D=0.8\text{A}$	-	7.2	8	Ω
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}$, $I_D=250\mu\text{A}$	2	-	4	V
g_f	Forward Transconductance	$V_{\text{DS}}=10\text{V}$, $I_D=0.8\text{A}$	-	0.8	-	S
I_{DSS}	Drain-Source Leakage Current ($T_j=25^\circ\text{C}$)	$V_{\text{DS}}=600\text{V}$, $V_{\text{GS}}=0\text{V}$	-	-	10	μA
	Drain-Source Leakage Current ($T_j=150^\circ\text{C}$)	$V_{\text{DS}}=480\text{V}$, $V_{\text{GS}}=0\text{V}$	-	-	100	μA
I_{GSS}	Gate-Source Leakage	$V_{\text{GS}}= \pm 30\text{V}$	-	-	± 100	nA
Q_g	Total Gate Charge ³	$I_D=1.6\text{A}$	-	7.7	-	nC
Q_{gs}	Gate-Source Charge	$V_{\text{DS}}=480\text{V}$	-	1.5	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	$V_{\text{GS}}=10\text{V}$	-	2.6	-	nC
$t_{d(\text{on})}$	Turn-on Delay Time ³	$V_{\text{DD}}=300\text{V}$	-	8	-	ns
t_r	Rise Time	$I_D=1.6\text{A}$	-	5	-	ns
$t_{d(\text{off})}$	Turn-off Delay Time	$R_G=10\Omega$, $V_{\text{GS}}=10\text{V}$	-	14	-	ns
t_f	Fall Time	$R_D=187.5\Omega$	-	7	-	ns
C_{iss}	Input Capacitance	$V_{\text{GS}}=0\text{V}$	-	286	-	pF
C_{oss}	Output Capacitance	$V_{\text{DS}}=25\text{V}$	-	25	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	6	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I_S	Continuous Source Current (Body Diode)	$V_D=V_G=0\text{V}$, $V_S=1.5\text{V}$	-	-	1.6	A
I_{SM}	Pulsed Source Current (Body Diode) ¹		-	-	6	A
V_{SD}	Forward On Voltage ³	$T_j=25^\circ\text{C}$, $I_S=1.6\text{A}$, $V_{\text{GS}}=0\text{V}$	-	-	1.5	V

Notes:

- 1.Pulse width limited by safe operating area.
- 2.Starting $T_j=25^\circ\text{C}$, $V_{\text{DD}}=50\text{V}$, $L=10\text{mH}$, $R_G=25\Omega$, $I_{\text{AS}}=1.6\text{A}$.
- 3.Pulse width $\leq 300\text{us}$, duty cycle $\leq 2\%$.

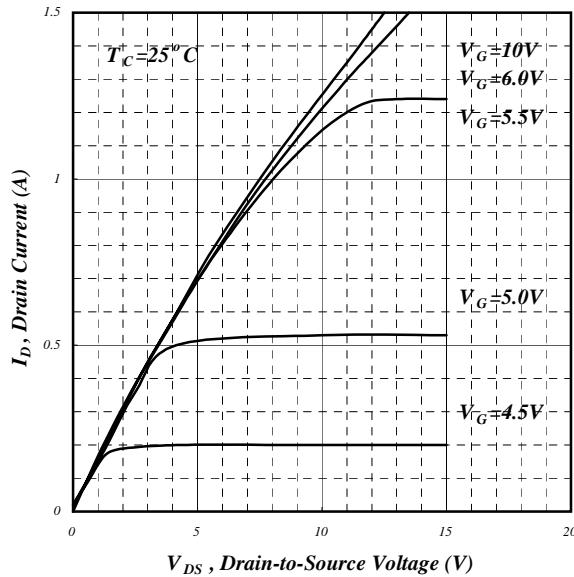


Fig 1. Typical Output Characteristics

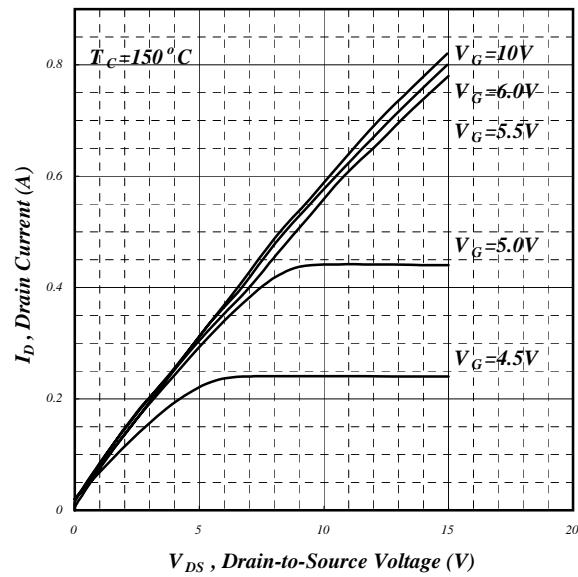


Fig 2. Typical Output Characteristics

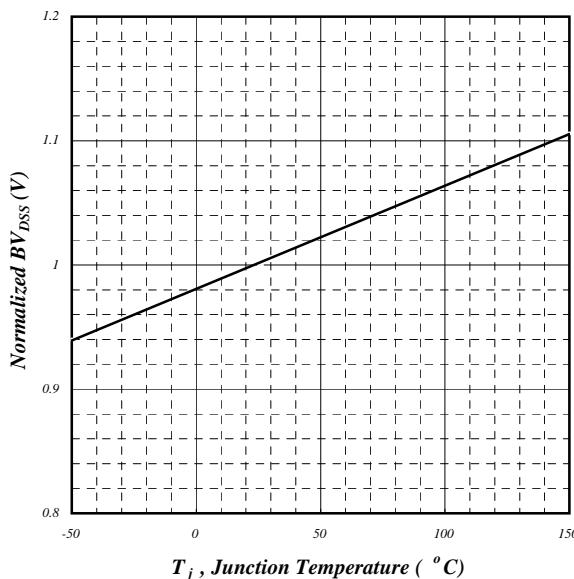
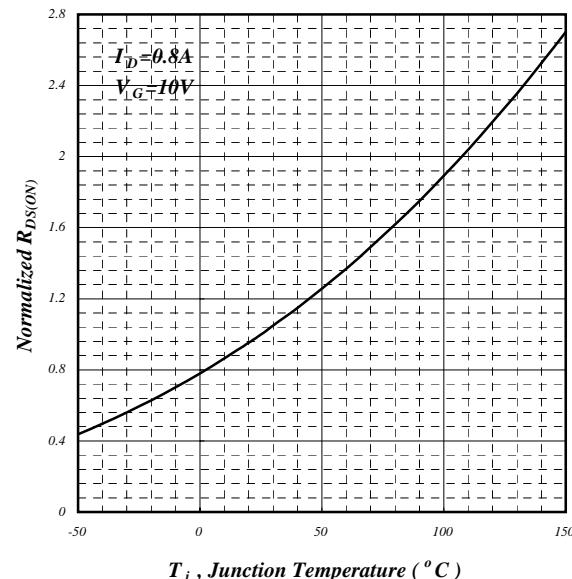

 Fig 3. Normalized BV_{DSS} vs. Junction Temperature


Fig 4. Normalized On-Resistance vs. Junction Temperature

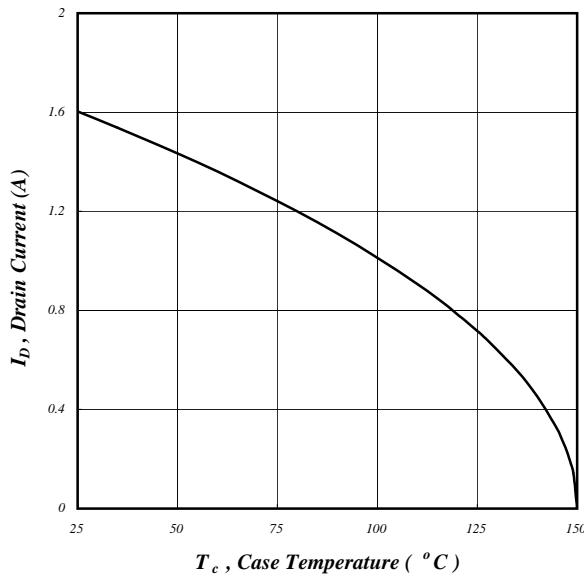


Fig 5. Maximum Drain Current vs.
Case Temperature

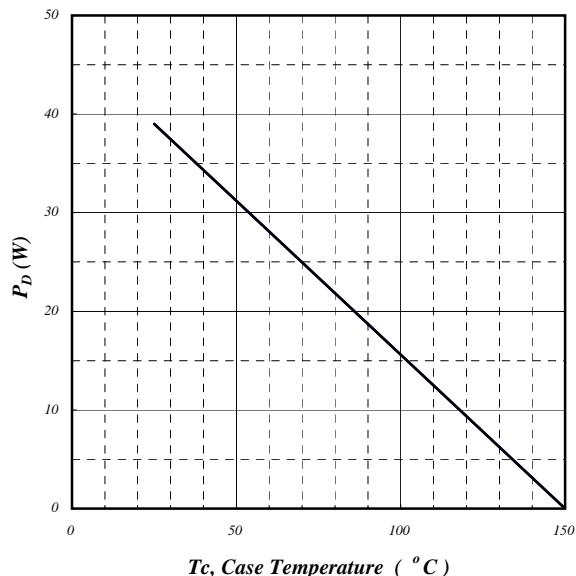


Fig 6. Typical Power Dissipation

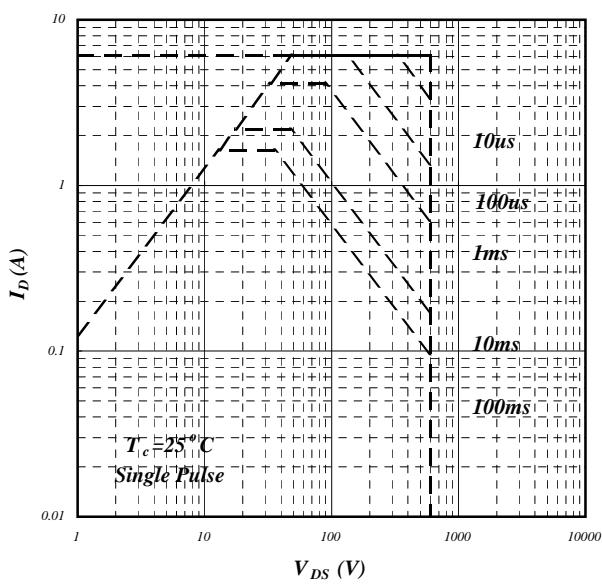


Fig 7. Maximum Safe Operating Area

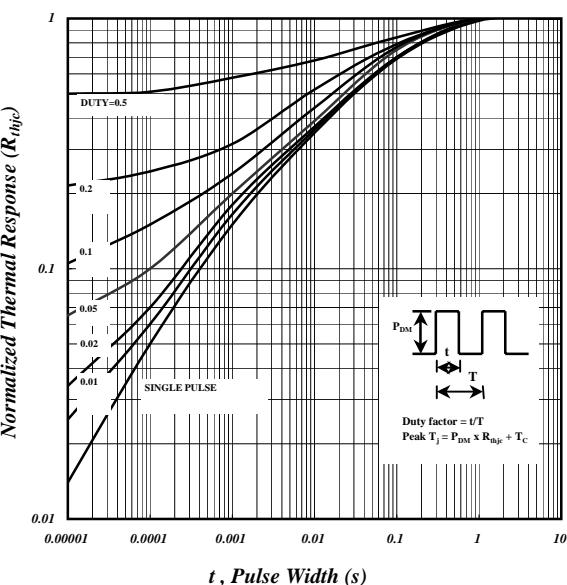


Fig 8. Effective Transient Thermal Impedance

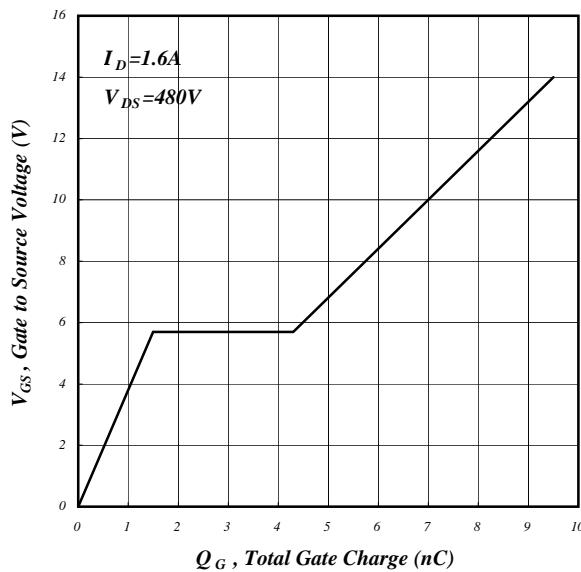


Fig 9. Gate Charge Characteristics

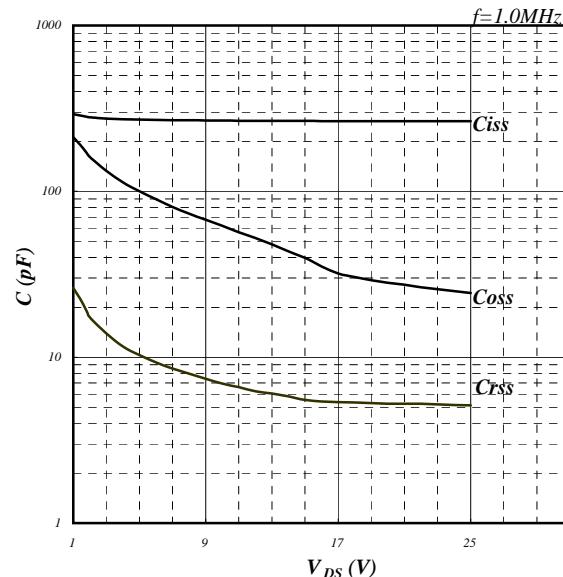


Fig 10. Typical Capacitance Characteristics

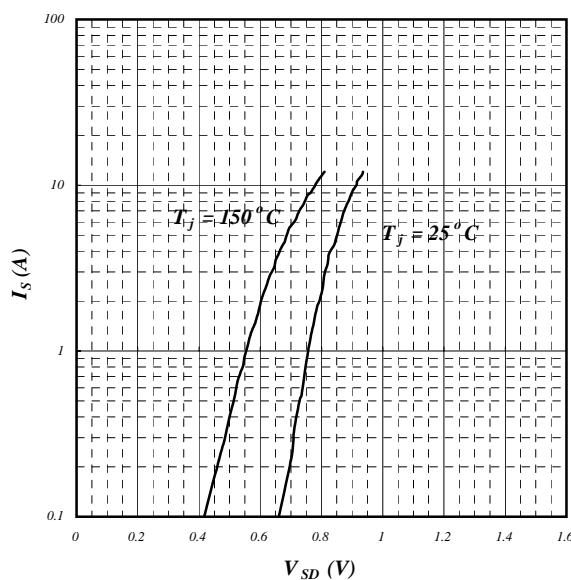


Fig 11. Forward Characteristic of Reverse Diode

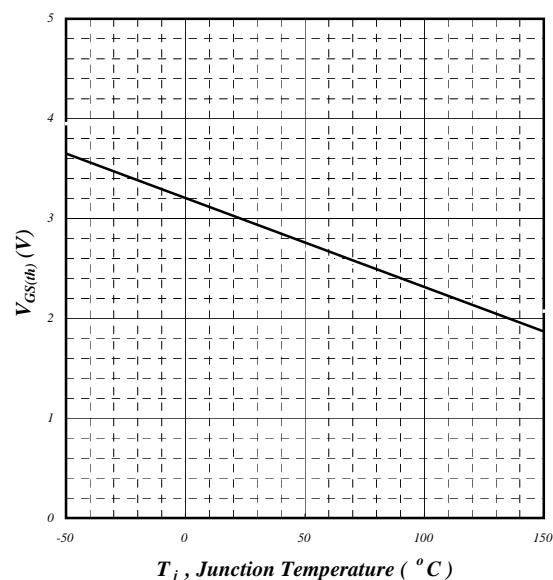


Fig 12. Gate Threshold Voltage vs. Junction Temperature

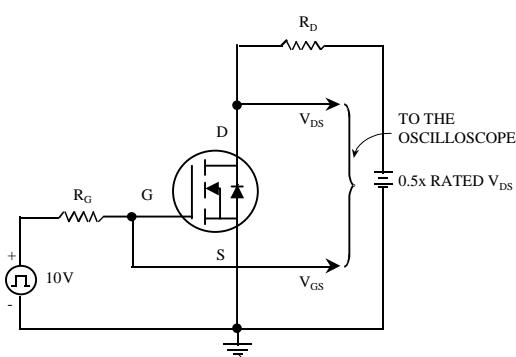


Fig 13. Switching Time Circuit

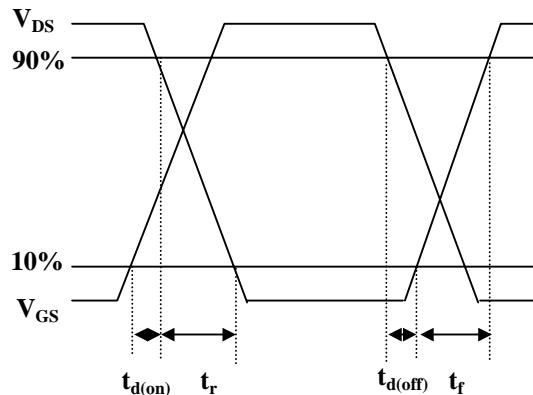


Fig 14. Switching Time Waveform

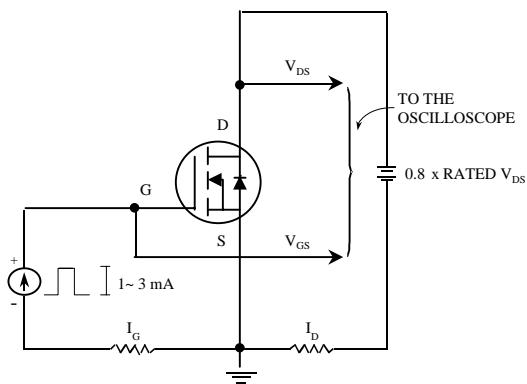


Fig 15. Gate Charge Circuit

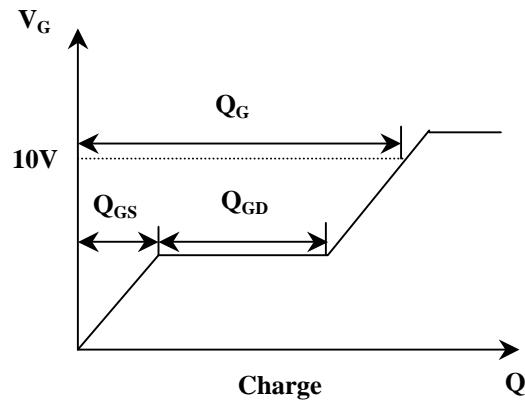


Fig 16. Gate Charge Waveform

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